

May 2013

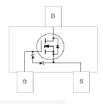
BSS138K

N-Channel Logic Level Enhancement Mode Field Effect Transistor

Features

- · Low On-Resistance
- · Low Gate Threshold Voltage
- · Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- · Pb Free / RoHS Compliant
- · Green Compound
- ESD HBM = 2000 V as per JEDEC A114A; ESD CDM = 2000 V as per JEDEC C101C





Absolute Maximum Ratings(1)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter		Value	Units
V _{DSS}	Drain-Source Voltage		50	V
V _{GSS}	Gate-Source Voltage	±12	V	
I _D	Drain Current	Continuous	0.22	Α
		Pulsed	0.88	A
T_J	Operating Junction Temperature Range		-55 to +150	°C
T _{STG}	Storage Temperature Range		-55 to +150	°C

Note:

1. These ratings are limiting values above which the serviceability of any semiconductor device maybe impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
В	Total Device Dissipation	350	mW
P _D	Derating above T _A = 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾	350	°C/W

Note:

2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size.

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
SK	BSS138K	7"	8 mm	3000 units

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
Off Chara	cteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	50			V	
BV _{DSS}	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to 25°C		0.11		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 50 V, V _{GS} = 0 V			0.1	μΑ	
		$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$			±1		
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$			±0.5	μΑ	
		$V_{GS} = \pm 5 \text{ V}, V_{DS} = 0 \text{ V}$			±0.05		
On Chara	cteristics						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.6		1.2	V	
V _{GS(th)}	Gate Threshold Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C		-1.4		mV/°C	
		$V_{GS} = 1.8V, I_D = 50 \text{ mA},$			2.5		
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 2.5 V, I _D = 50 mA			2.0	Ω	
	On-Resistance	$V_{GS} = 5V, I_D = 50 \text{ mA}$			1.6		
I _{D(ON)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	0.2			Α	
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 200 mA	200			mS	
Dynamic	Characteristics						
C _{iss}	Input Capacitance			58			
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		9.75		pF	
C _{rss}	Reverse Transfer Capacitance	1 - 1.5 WH 12		5.2			
R _G	Gate Resistance	V _{DS} = 5 V, V _{GS} = 10 mV		281		Ω	
Switching	Characteristics						
t _{D(ON)}	Turn-On Delay Time			P	5		
t _r	Turn-On Rise Time	$V_{DD} = 30 \text{ V, } I_{D} = 0.29 \text{ A,}$ $V_{GS} = 10 \text{ V, } R_{GEN} = 6 \Omega$			5	ns ns	
t _{D(OFF)}	Turn-Off Delay Time				60		
t _f	Turn-Off Fall Time				35		
Q_g	Total Gate Change	V 05.V.L 0.0.A			2.4		
Q _{gs}	Gate-Source Change	$V_{DS} = 25 \text{ V}, I_{D} = 0.2 \text{ A},$ $V_{GS} = 10 \text{ V}, I_{G} = 0.1 \text{ mA}$			0.5	nC	
Q_{gd}	Gate-Drain Change	1.03 .0 ., 16 - 511 1111			0.5	0.5	
Drain-Sou	irce Diode Characteristics and	d Maximum Ratings					
V _{sd}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 115 mA			1.2	V	

Typical Performance Characteristics

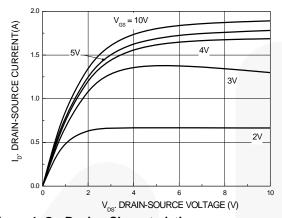


Figure 1. On-Region Characteristics

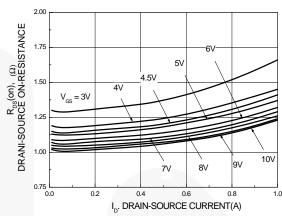


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

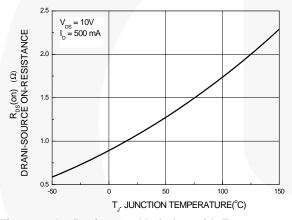
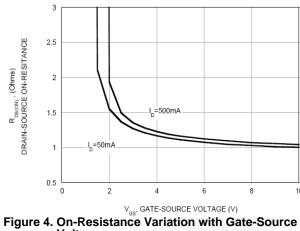


Figure 3. On-Resistance Variation with Temperature



Voltage

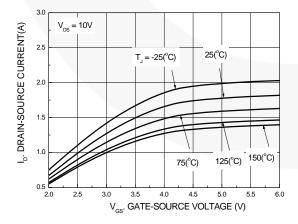


Figure 5. Transfer Characteristics

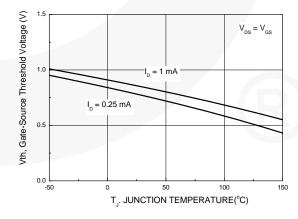


Figure 6. Gate Threshold Variation with Temperature

Typical Performance Characteristics (Continue)

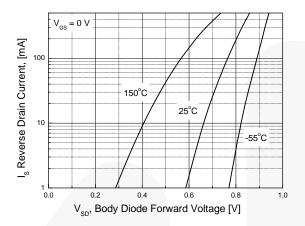


Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

Physical Dimensions

SOT-23

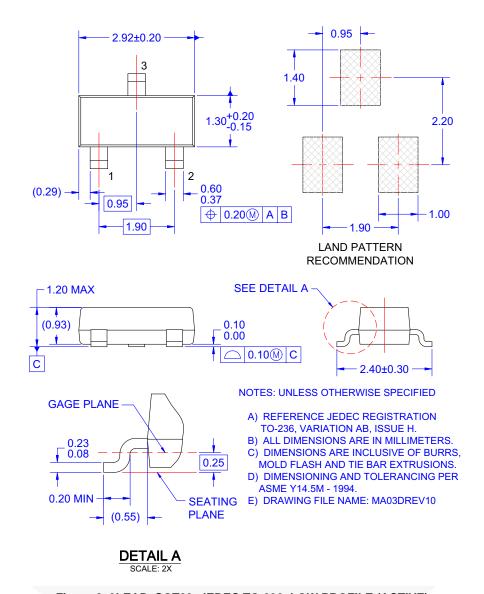


Figure 8. 3LEAD, SOT23, JEDEC TO-236, LOW PROFILE (ACTIVE)

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Definition of Torms

Definition of Terms				
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